

## IGBT

Low  $V_{CE(sat)}$  IGBT in TRENCHSTOP™ 5 technology copacked with RAPID 1 fast and soft antiparallel diode

## IKW75N65EL5

650V DuoPack IGBT and diode  
Low  $V_{CE(sat)}$  series fifth generation

Data sheet

Low  $V_{CE(sat)}$  series fifth generation

Low  $V_{CE(sat)}$  IGBT in TRENCHSTOP™ 5 technology copacked with RAPID 1 fast and soft antiparallel diode

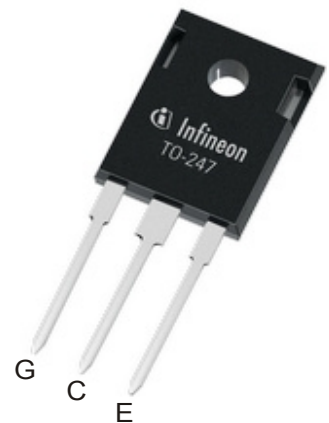
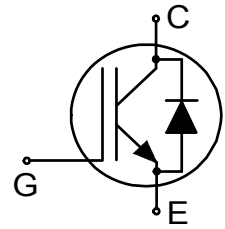
#### Features and Benefits:

Low  $V_{CE(sat)}$  L5 technology offering

- Very low collector-emitter saturation voltage  $V_{CEsat}$
- Best-in-Class tradeoff between conduction and switching losses
- 650V breakdown voltage
- Low gate charge  $Q_G$
- Maximum junction temperature 175°C
- Qualified according to JEDEC for target applications
- Pb-free lead plating
- RoHS compliant
- Complete product spectrum and PSpice models:  
<http://www.infineon.com/igbt/>

#### Applications:

- Uninterruptible power supplies
- Solar photovoltaic inverters
- Welding machines



#### Key Performance and Package Parameters

| Type        | $V_{CE}$ | $I_C$ | $V_{CEsat}$ , $T_{vj}=25^\circ\text{C}$ | $T_{vjmax}$ | Marking | Package    |
|-------------|----------|-------|-----------------------------------------|-------------|---------|------------|
| IKW75N65EL5 | 650V     | 75A   | 1.1V                                    | 175°C       | K75EEL5 | PG-TO247-3 |

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Low  $V_{CE(sat)}$  series fifth generation

## Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

| Parameter                                                                                                                            | Symbol      | Value                | Unit               |
|--------------------------------------------------------------------------------------------------------------------------------------|-------------|----------------------|--------------------|
| Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$                                                                          | $V_{CE}$    | 650                  | V                  |
| DC collector current, limited by $T_{vjmax}^{1)}$<br>$T_c = 25^{\circ}\text{C}$<br>$T_c = 100^{\circ}\text{C}$                       | $I_C$       | 80.0<br>80.0         | A                  |
| Pulsed collector current, $t_p$ limited by $T_{vjmax}^{2)}$                                                                          | $I_{Cpuls}$ | 300.0                | A                  |
| Turn off safe operating area<br>$V_{CE} \leq 650\text{V}$ , $T_{vj} \leq 175^{\circ}\text{C}$ , $t_p = 1\mu\text{s}^{2)}$            | -           | 300.0                | A                  |
| Diode forward current, limited by $T_{vjmax}$<br>$T_c = 25^{\circ}\text{C}$ value limited by bondwire<br>$T_c = 100^{\circ}\text{C}$ | $I_F$       | 90.0<br>89.0         | A                  |
| Diode pulsed current, $t_p$ limited by $T_{vjmax}^{2)}$                                                                              | $I_{Fpuls}$ | 300.0                | A                  |
| Gate-emitter voltage<br>Transient Gate-emitter voltage ( $t_p \leq 10\mu\text{s}$ , $D < 0.010$ )                                    | $V_{GE}$    | $\pm 20$<br>$\pm 30$ | V                  |
| Power dissipation $T_c = 25^{\circ}\text{C}$<br>Power dissipation $T_c = 100^{\circ}\text{C}$                                        | $P_{tot}$   | 536.0<br>268.0       | W                  |
| Operating junction temperature                                                                                                       | $T_{vj}$    | $-40 \dots +175$     | $^{\circ}\text{C}$ |
| Storage temperature                                                                                                                  | $T_{stg}$   | $-55 \dots +150$     | $^{\circ}\text{C}$ |
| Soldering temperature, <sup>3)</sup><br>wave soldering 1.6mm (0.063in.) from case for 10s                                            |             | 260                  | $^{\circ}\text{C}$ |
| Mounting torque, M3 screw<br>Maximum of mounting processes: 3                                                                        | $M$         | 0.6                  | Nm                 |

## Thermal Resistance

| Parameter                                    | Symbol               | Conditions | Value |      |      | Unit |
|----------------------------------------------|----------------------|------------|-------|------|------|------|
|                                              |                      |            | min.  | typ. | max. |      |
| R <sub>th</sub> Characteristics              |                      |            |       |      |      |      |
| IGBT thermal resistance,<br>junction - case  | R <sub>th(j-c)</sub> |            | -     | -    | 0.28 | K/W  |
| Diode thermal resistance,<br>junction - case | R <sub>th(j-c)</sub> |            | -     | -    | 0.46 | K/W  |
| Thermal resistance<br>junction - ambient     | R <sub>th(j-a)</sub> |            | -     | -    | 40   | K/W  |

<sup>1)</sup> Both values limited by bondwires.

<sup>2)</sup> Defined by design. Not subject to production test.

<sup>3)</sup> Package not recommended for surface mount applications.

Low  $V_{CE(sat)}$  series fifth generationElectrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified

| Parameter                            | Symbol        | Conditions                                                                                                    | Value       |                      |                | Unit    |
|--------------------------------------|---------------|---------------------------------------------------------------------------------------------------------------|-------------|----------------------|----------------|---------|
|                                      |               |                                                                                                               | min.        | typ.                 | max.           |         |
| Static Characteristic                |               |                                                                                                               |             |                      |                |         |
| Collector-emitter breakdown voltage  | $V_{(BR)CES}$ | $V_{GE} = 0V, I_C = 0.20mA$                                                                                   | 650         | -                    | -              | V       |
| Collector-emitter saturation voltage | $V_{CEsat}$   | $V_{GE} = 15.0V, I_C = 75.0A$<br>$T_{vj} = 25^{\circ}C$<br>$T_{vj} = 100^{\circ}C$<br>$T_{vj} = 150^{\circ}C$ | -<br>-<br>- | 1.10<br>1.11<br>1.12 | 1.35<br>-<br>- | V       |
| Diode forward voltage                | $V_F$         | $V_{GE} = 0V, I_F = 75.0A$<br>$T_{vj} = 25^{\circ}C$<br>$T_{vj} = 100^{\circ}C$<br>$T_{vj} = 150^{\circ}C$    | -<br>-<br>- | 1.40<br>1.42<br>1.40 | 1.70<br>-<br>- | V       |
| Gate-emitter threshold voltage       | $V_{GE(th)}$  | $I_C = 1.00mA, V_{CE} = 20V$                                                                                  | 4.2         | 5.0                  | 5.8            | V       |
| Zero gate voltage collector current  | $I_{CES}$     | $V_{CE} = 650V, V_{GE} = 0V$<br>$T_{vj} = 25^{\circ}C$<br>$T_{vj} = 150^{\circ}C$<br>$T_{vj} = 175^{\circ}C$  | -<br>-<br>- | -<br>1000<br>5000    | 40<br>-<br>-   | $\mu A$ |
| Gate-emitter leakage current         | $I_{GES}$     | $V_{CE} = 0V, V_{GE} = 20V$                                                                                   | -           | -                    | 100            | nA      |
| Transconductance                     | $g_{fs}$      | $V_{CE} = 20V, I_C = 75.0A$                                                                                   | -           | 155.0                | -              | S       |

Electrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified

| Parameter                                                            | Symbol           | Conditions                                                               | Value |       |      | Unit |
|----------------------------------------------------------------------|------------------|--------------------------------------------------------------------------|-------|-------|------|------|
|                                                                      |                  |                                                                          | min.  | typ.  | max. |      |
| Dynamic Characteristic                                               |                  |                                                                          |       |       |      |      |
| Input capacitance                                                    | C <sub>ies</sub> | V <sub>CE</sub> = 25V, V <sub>GE</sub> = 0V<br>f = 1000kHz               | -     | 12100 | -    | pF   |
| Output capacitance                                                   | C <sub>oes</sub> |                                                                          | -     | 150   | -    |      |
| Reverse transfer capacitance                                         | C <sub>res</sub> |                                                                          | -     | 42    | -    |      |
| Gate charge                                                          | Q <sub>G</sub>   | V <sub>CC</sub> = 520V, I <sub>C</sub> = 75.0A,<br>V <sub>GE</sub> = 15V | -     | 436.0 | -    | nC   |
| Internal emitter inductance<br>measured 5mm (0.197 in.) from<br>case | L <sub>E</sub>   |                                                                          | -     | 13.0  | -    | nH   |

Switching Characteristic, Inductive Load

| Parameter                                             | Symbol              | Conditions                                                                                                                                                                                                                                                                                                                         | Value |      |      | Unit |
|-------------------------------------------------------|---------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------|------|------|------|
|                                                       |                     |                                                                                                                                                                                                                                                                                                                                    | min.  | typ. | max. |      |
| IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$ |                     |                                                                                                                                                                                                                                                                                                                                    |       |      |      |      |
| Turn-on delay time                                    | $t_{d(\text{on})}$  | $T_{vj} = 25^{\circ}\text{C},$<br>$V_{CC} = 400\text{V}, I_C = 75.0\text{A},$<br>$V_{GE} = 0.0/15.0\text{V},$<br>$R_{G(\text{on})} = 4.0\Omega, R_{G(\text{off})} = 4.0\Omega,$<br>$L\sigma = 40\text{nH}, C\sigma = 30\text{pF}$<br>$L\sigma, C\sigma$ from Fig. E<br>Energy losses include “tail” and<br>diode reverse recovery. | -     | 40   | -    | ns   |
| Rise time                                             | $t_r$               |                                                                                                                                                                                                                                                                                                                                    | -     | 11   | -    | ns   |
| Turn-off delay time                                   | $t_{d(\text{off})}$ |                                                                                                                                                                                                                                                                                                                                    | -     | 275  | -    | ns   |
| Fall time                                             | $t_f$               |                                                                                                                                                                                                                                                                                                                                    | -     | 50   | -    | ns   |
| Turn-on energy                                        | $E_{\text{on}}$     |                                                                                                                                                                                                                                                                                                                                    | -     | 1.61 | -    | mJ   |
| Turn-off energy                                       | $E_{\text{off}}$    |                                                                                                                                                                                                                                                                                                                                    | -     | 3.20 | -    | mJ   |
| Total switching energy                                | $E_{\text{ts}}$     |                                                                                                                                                                                                                                                                                                                                    | -     | 4.81 | -    | mJ   |

Low  $V_{CE(sat)}$  series fifth generationDiode Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ 

|                                                                  |              |                                                                                                                         |   |       |   |                        |
|------------------------------------------------------------------|--------------|-------------------------------------------------------------------------------------------------------------------------|---|-------|---|------------------------|
| Diode reverse recovery time                                      | $t_{rr}$     | $T_{vj} = 25^{\circ}\text{C},$<br>$V_R = 400\text{V},$<br>$I_F = 75.0\text{A},$<br>$di_F/dt = 1500\text{A}/\mu\text{s}$ | - | 114   | - | ns                     |
| Diode reverse recovery charge                                    | $Q_{rr}$     |                                                                                                                         | - | 1.37  | - | $\mu\text{C}$          |
| Diode peak reverse recovery current                              | $I_{rrm}$    |                                                                                                                         | - | 29.0  | - | A                      |
| Diode peak rate of fall of reverse recovery current during $t_b$ | $di_{rr}/dt$ |                                                                                                                         | - | -2170 | - | $\text{A}/\mu\text{s}$ |

## Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value |      |      | Unit |
|-----------|--------|------------|-------|------|------|------|
|           |        |            | min.  | typ. | max. |      |

IGBT Characteristic, at  $T_{vj} = 150^{\circ}\text{C}$ 

|                        |              |                                                                                                                                                                                                                                                                                  |   |      |   |    |
|------------------------|--------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---|------|---|----|
| Turn-on delay time     | $t_{d(on)}$  | $T_{vj} = 150^{\circ}\text{C},$<br>$V_{CC} = 400\text{V}, I_C = 75.0\text{A},$<br>$V_{GE} = 0.0/15.0\text{V},$<br>$R_{G(on)} = 4.0\Omega, R_{G(off)} = 4.0\Omega,$<br>$L\sigma = 40\text{nH}, C\sigma = 30\text{pF}$<br>Energy losses include "tail" and diode reverse recovery. | - | 39   | - | ns |
| Rise time              | $t_r$        |                                                                                                                                                                                                                                                                                  | - | 14   | - | ns |
| Turn-off delay time    | $t_{d(off)}$ |                                                                                                                                                                                                                                                                                  | - | 330  | - | ns |
| Fall time              | $t_f$        |                                                                                                                                                                                                                                                                                  | - | 144  | - | ns |
| Turn-on energy         | $E_{on}$     |                                                                                                                                                                                                                                                                                  | - | 2.12 | - | mJ |
| Turn-off energy        | $E_{off}$    |                                                                                                                                                                                                                                                                                  | - | 5.10 | - | mJ |
| Total switching energy | $E_{ts}$     |                                                                                                                                                                                                                                                                                  | - | 7.22 | - | mJ |

Diode Characteristic, at  $T_{vj} = 150^{\circ}\text{C}$ 

|                                                                  |              |                                                                                                                          |   |       |   |                        |
|------------------------------------------------------------------|--------------|--------------------------------------------------------------------------------------------------------------------------|---|-------|---|------------------------|
| Diode reverse recovery time                                      | $t_{rr}$     | $T_{vj} = 150^{\circ}\text{C},$<br>$V_R = 400\text{V},$<br>$I_F = 75.0\text{A},$<br>$di_F/dt = 1500\text{A}/\mu\text{s}$ | - | 95    | - | ns                     |
| Diode reverse recovery charge                                    | $Q_{rr}$     |                                                                                                                          | - | 2.43  | - | $\mu\text{C}$          |
| Diode peak reverse recovery current                              | $I_{rrm}$    |                                                                                                                          | - | 40.0  | - | A                      |
| Diode peak rate of fall of reverse recovery current during $t_b$ | $di_{rr}/dt$ |                                                                                                                          | - | -2900 | - | $\text{A}/\mu\text{s}$ |

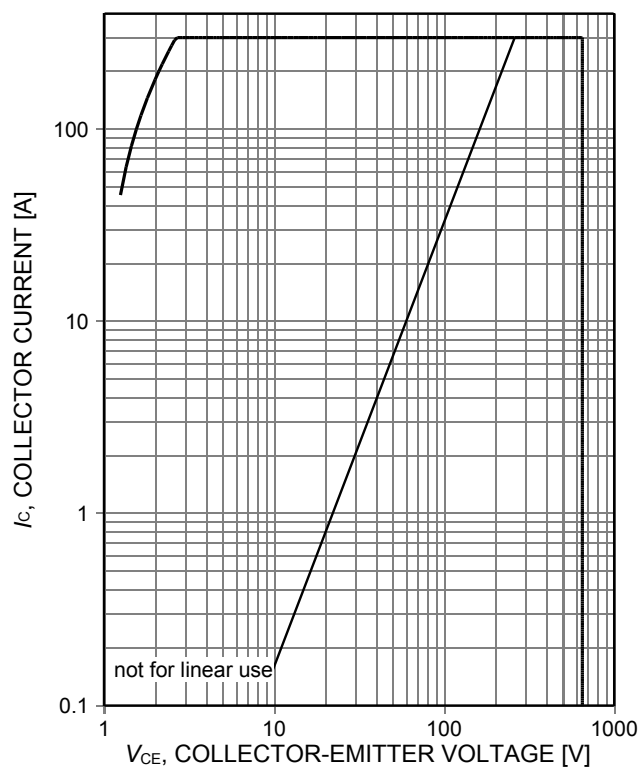
Low  $V_{CE(sat)}$  series fifth generation

Figure 1. **Forward bias safe operating area**  
( $D=0$ ,  $T_C=25^\circ\text{C}$ ,  $T_{vj}\leq 175^\circ\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $t_p=1\mu\text{s}$ ,  
 $I_{Cmax}$  defined by design - not subject to  
production test)

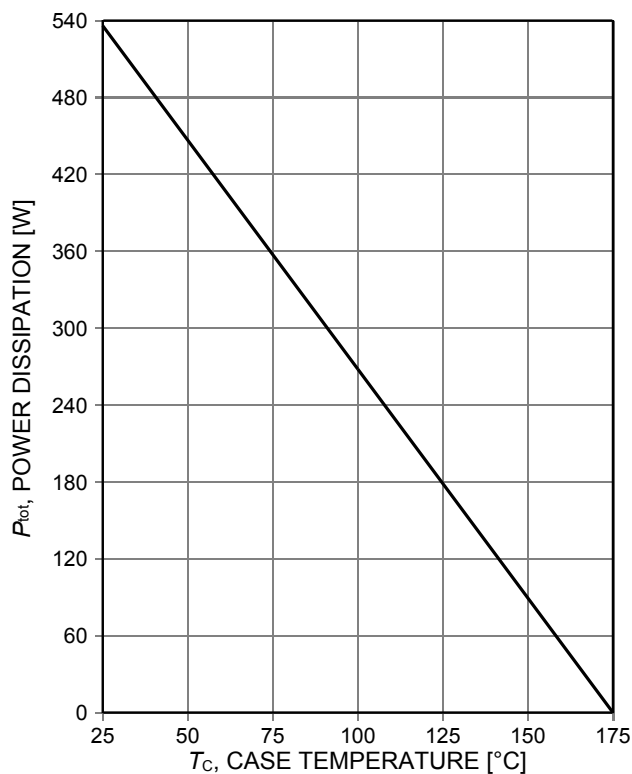


Figure 2. **Power dissipation as a function of case temperature**  
( $T_{vj}\leq 175^\circ\text{C}$ )

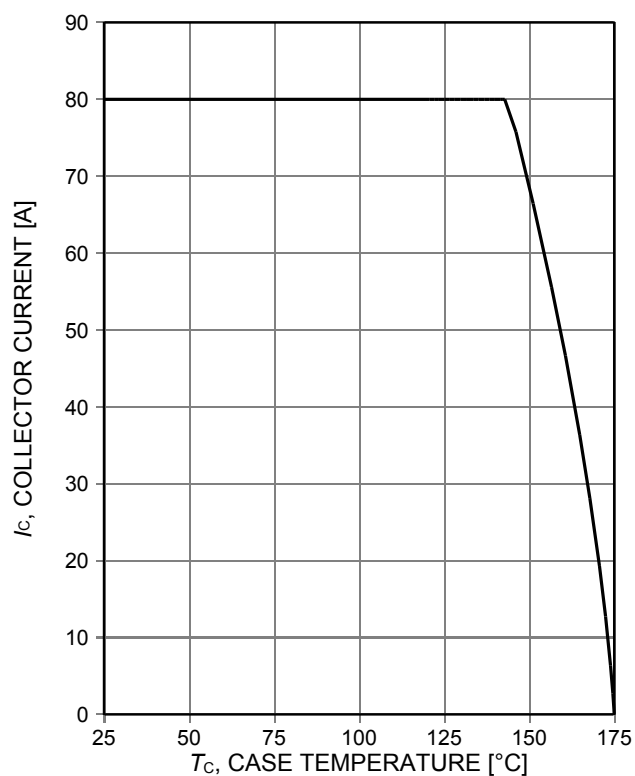


Figure 3. **Collector current as a function of case temperature**  
( $V_{GE}\geq 15\text{V}$ ,  $T_{vj}\leq 175^\circ\text{C}$ )

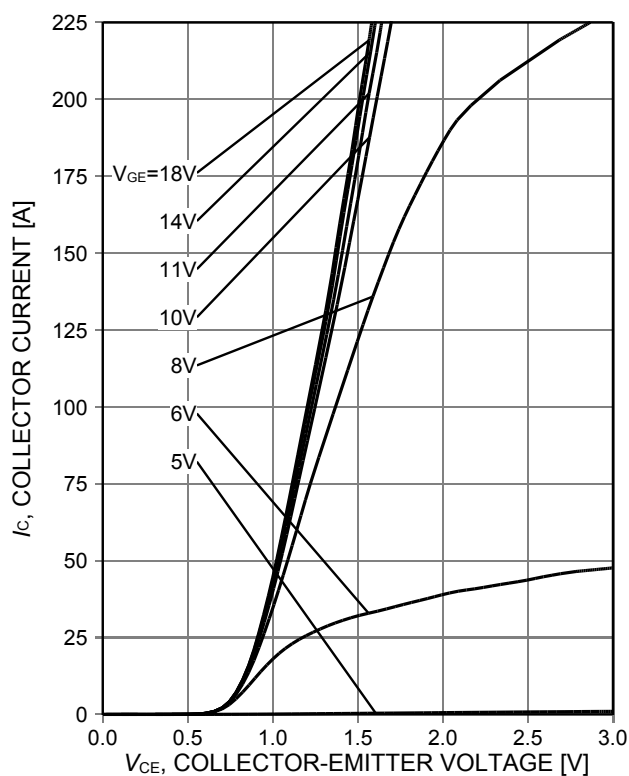
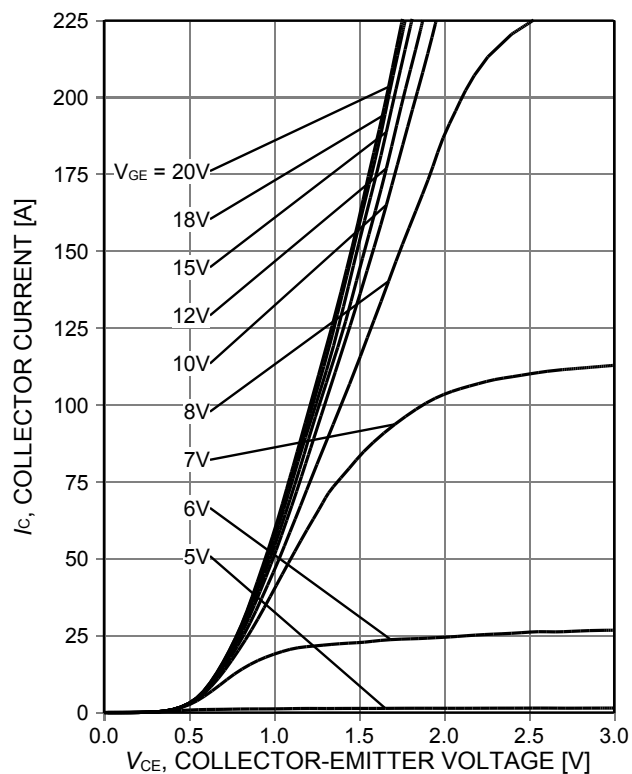
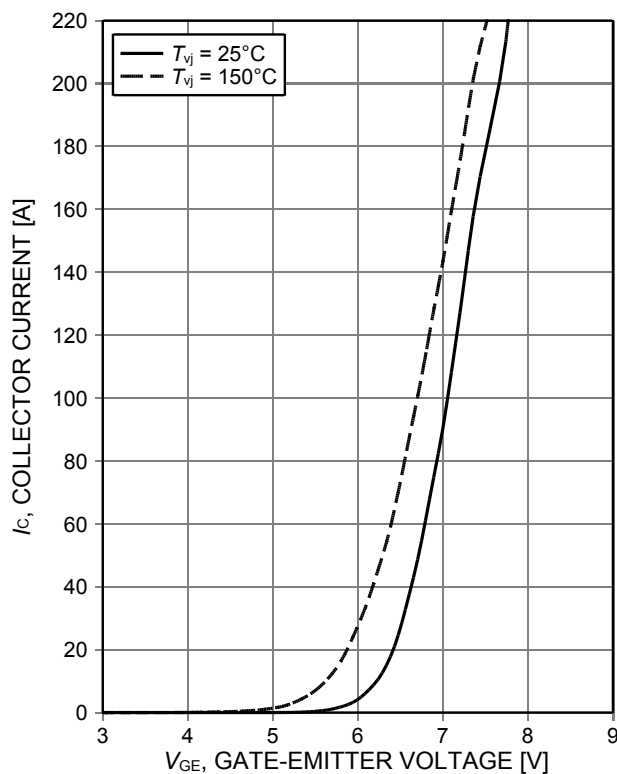
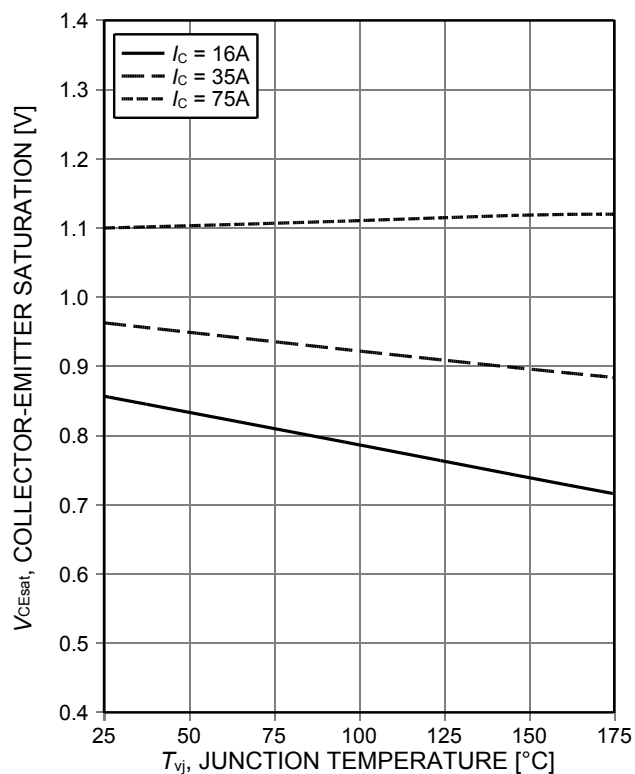
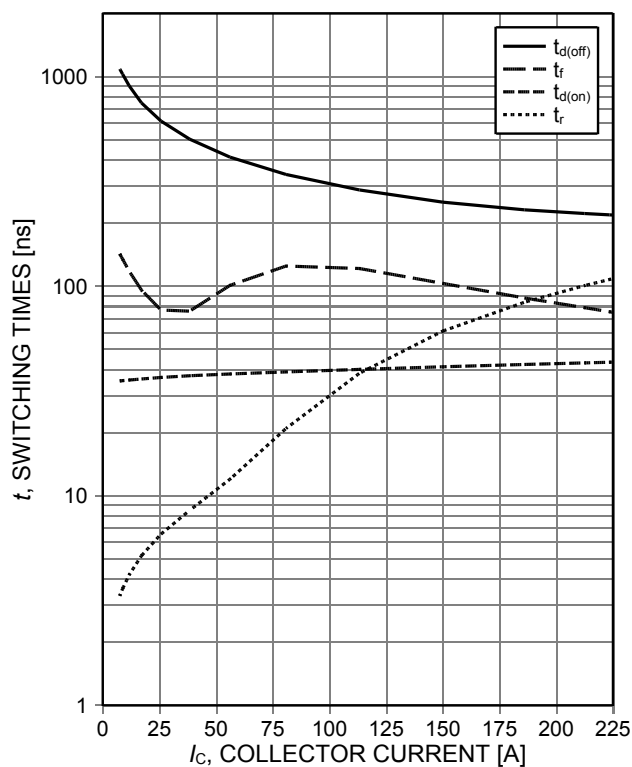


Figure 4. **Typical output characteristic**  
( $T_{vj}=25^\circ\text{C}$ )

Low  $V_{CE(sat)}$  series fifth generationFigure 5. **Typical output characteristic**  
( $T_{vj}=175^{\circ}\text{C}$ )Figure 6. **Typical transfer characteristic**  
( $V_{CE}=20\text{V}$ )Figure 7. **Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE}=15\text{V}$ )Figure 8. **Typical switching times as a function of collector current**  
(inductive load,  $T_{vj}=150^{\circ}\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_{G(on)}=4\Omega$ ,  $R_{G(off)}=4\Omega$ , dynamic test circuit in Figure E)

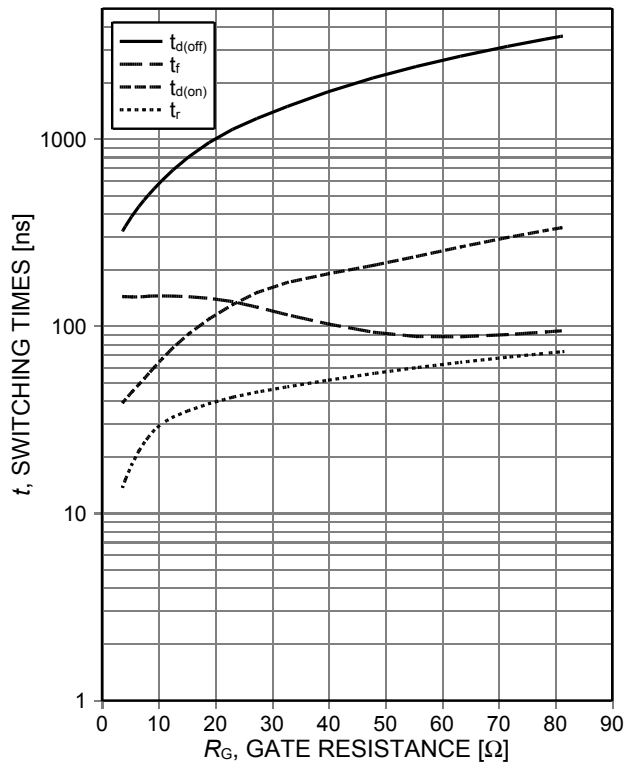
Low  $V_{CE(sat)}$  series fifth generation

Figure 9. **Typical switching times as a function of gate resistance**  
(inductive load,  $T_{vj}=150^{\circ}\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=75\text{A}$ , dynamic test circuit in Figure E)

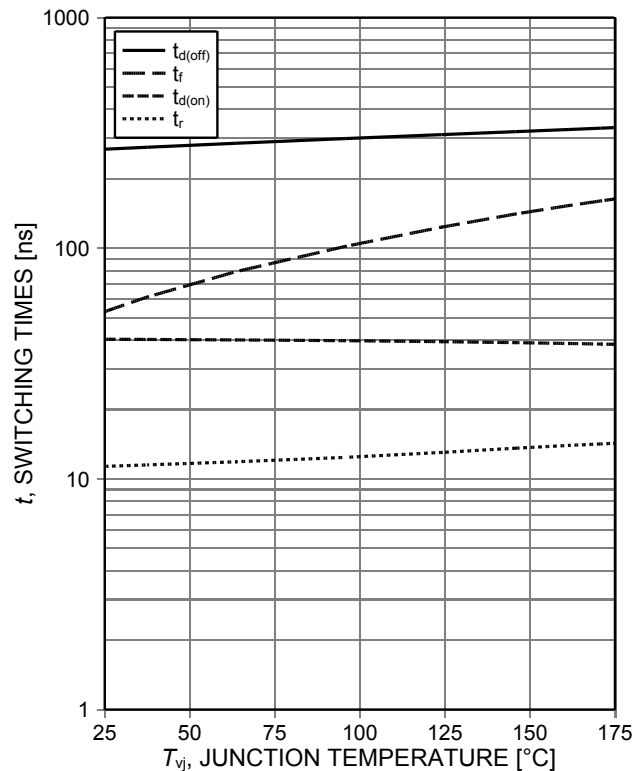


Figure 10. **Typical switching times as a function of junction temperature**  
(inductive load,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=75\text{A}$ ,  $R_{G(on)}=4\Omega$ ,  $R_{G(off)}=4\Omega$ , dynamic test circuit in Figure E)

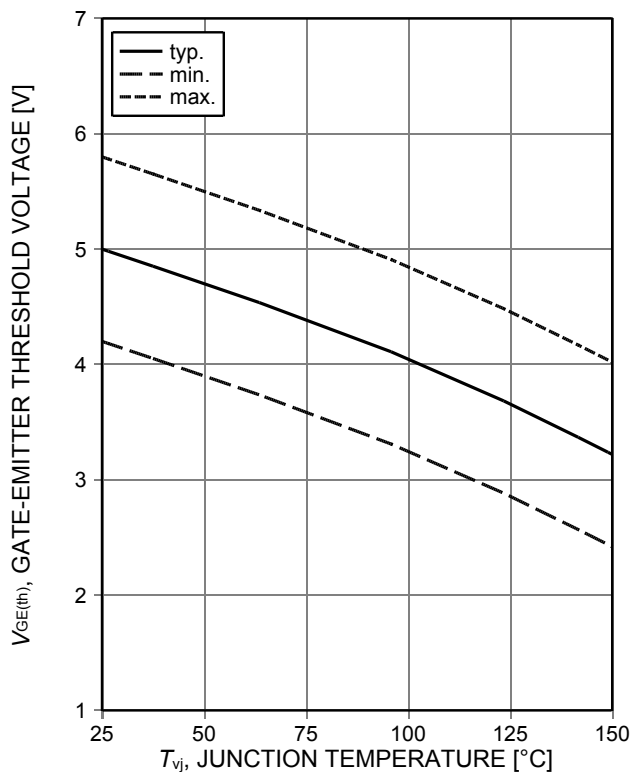


Figure 11. **Gate-emitter threshold voltage as a function of junction temperature**  
( $I_C=1\text{mA}$ )

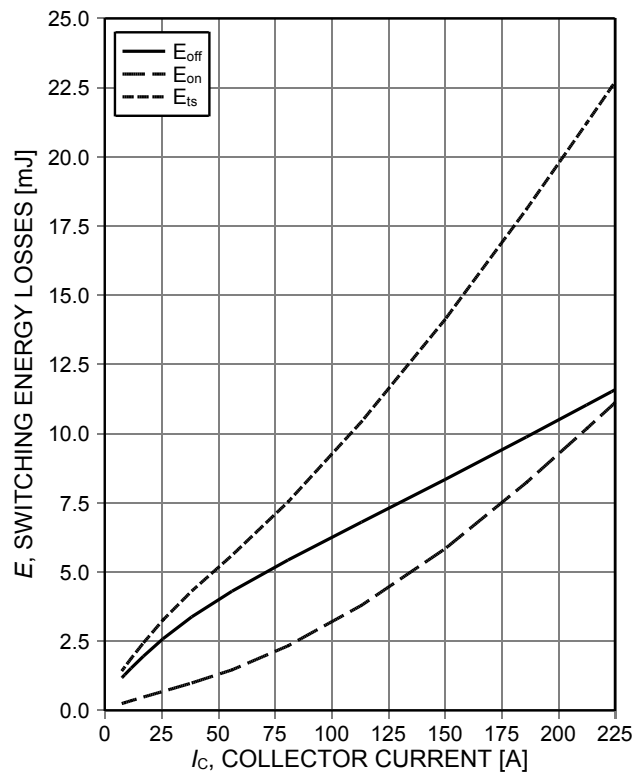


Figure 12. **Typical switching energy losses as a function of collector current**  
(inductive load,  $T_{vj}=150^{\circ}\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_{G(on)}=4\Omega$ ,  $R_{G(off)}=4\Omega$ , dynamic test circuit in Figure E)

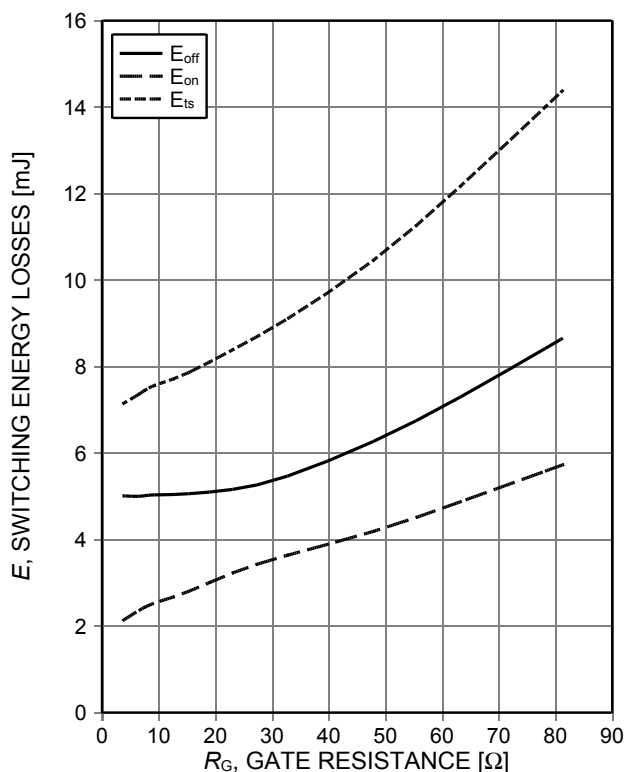
Low  $V_{CE(sat)}$  series fifth generation

Figure 13. **Typical switching energy losses as a function of gate resistance**  
(inductive load,  $T_{vj}=150^\circ\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=75\text{A}$ , dynamic test circuit in Figure E)

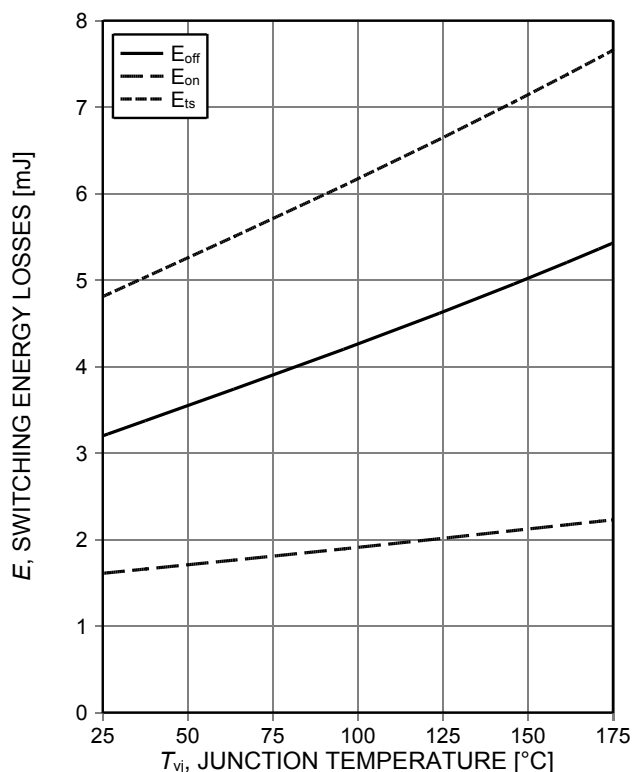


Figure 14. **Typical switching energy losses as a function of junction temperature**  
(inductive load,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=75\text{A}$ ,  $R_{G(on)}=4\Omega$ ,  $R_{G(off)}=4\Omega$ , dynamic test circuit in Figure E)

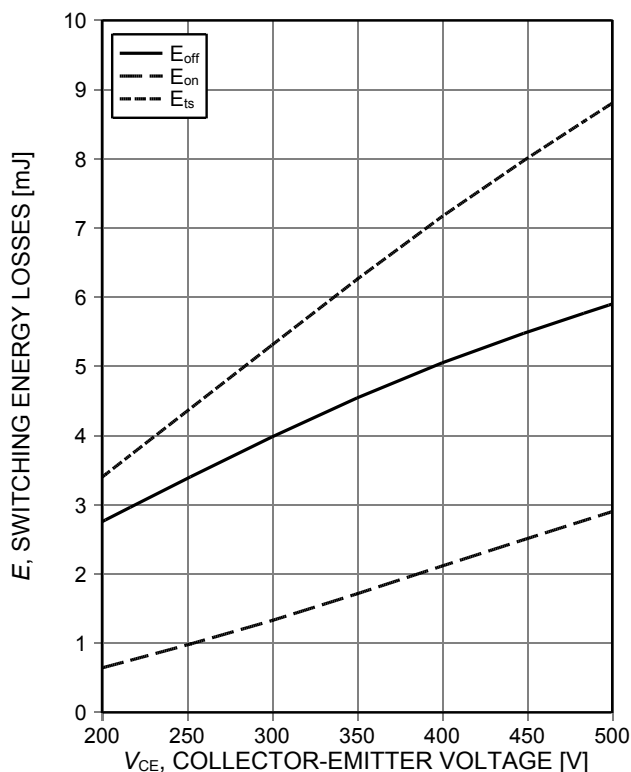


Figure 15. **Typical switching energy losses as a function of collector emitter voltage**  
(inductive load,  $T_{vj}=150^\circ\text{C}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=75\text{A}$ ,  $R_{G(on)}=4\Omega$ ,  $R_{G(off)}=4\Omega$ , dynamic test circuit in Figure E)

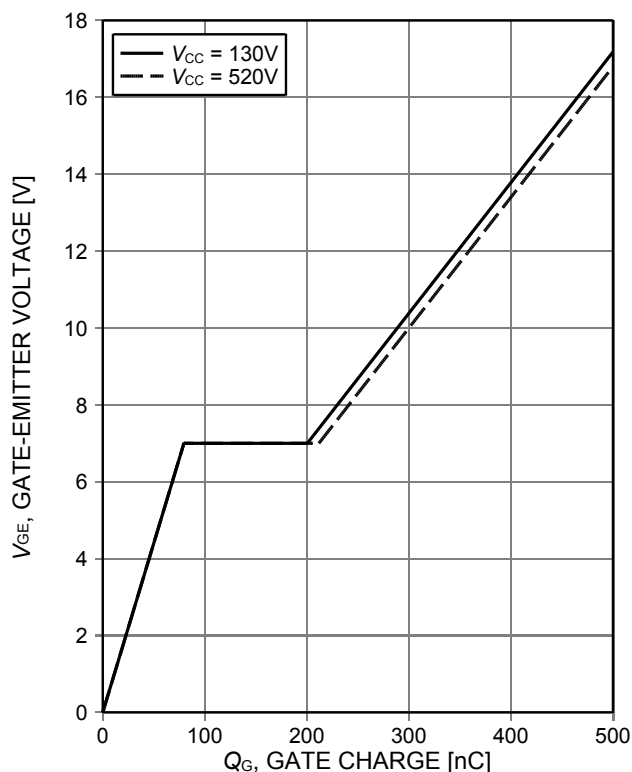


Figure 16. **Typical gate charge**  
( $I_C=75\text{A}$ )

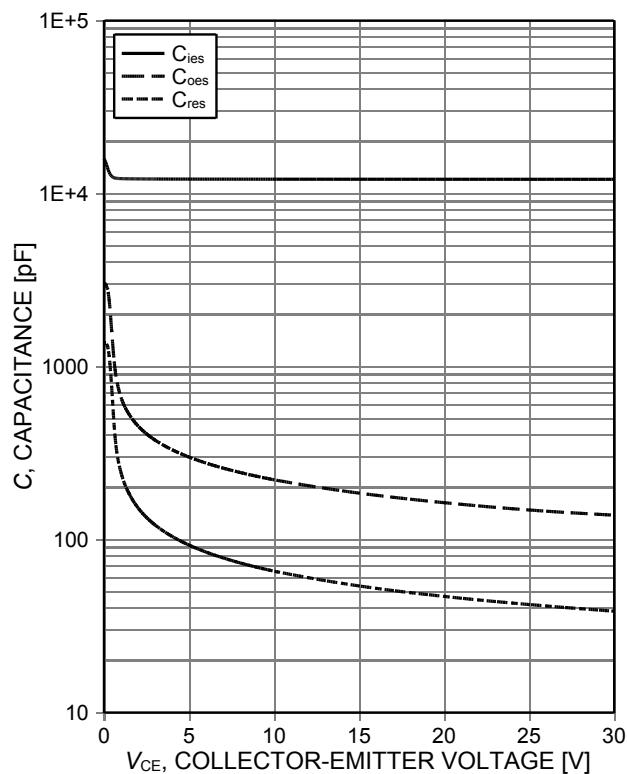
Low  $V_{CE(sat)}$  series fifth generation

Figure 17. Typical capacitance as a function of collector-emitter voltage ( $V_{GE}=0V$ ,  $f=1MHz$ )

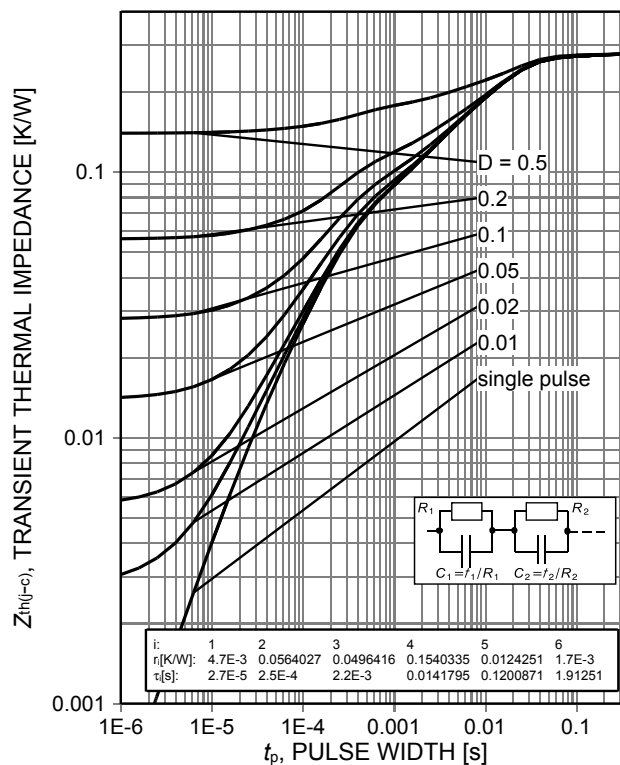


Figure 18. IGBT transient thermal impedance ( $D=t_p/T$ )

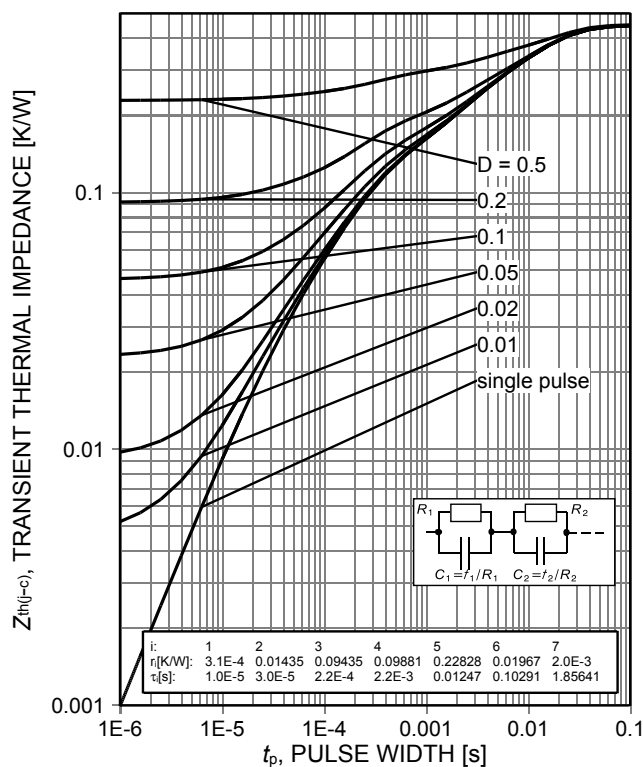


Figure 19. Diode transient thermal impedance as a function of pulse width ( $D=t_p/T$ )

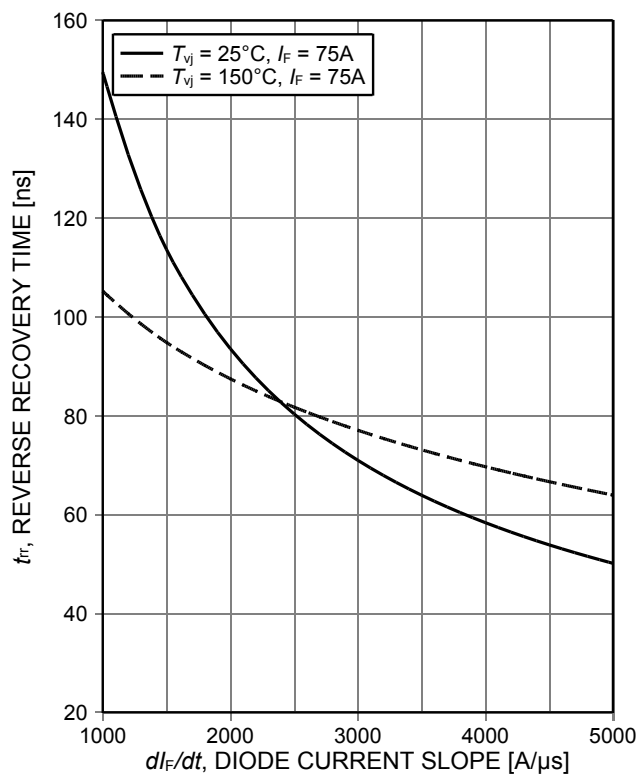


Figure 20. Typical reverse recovery time as a function of diode current slope ( $V_R=400V$ )

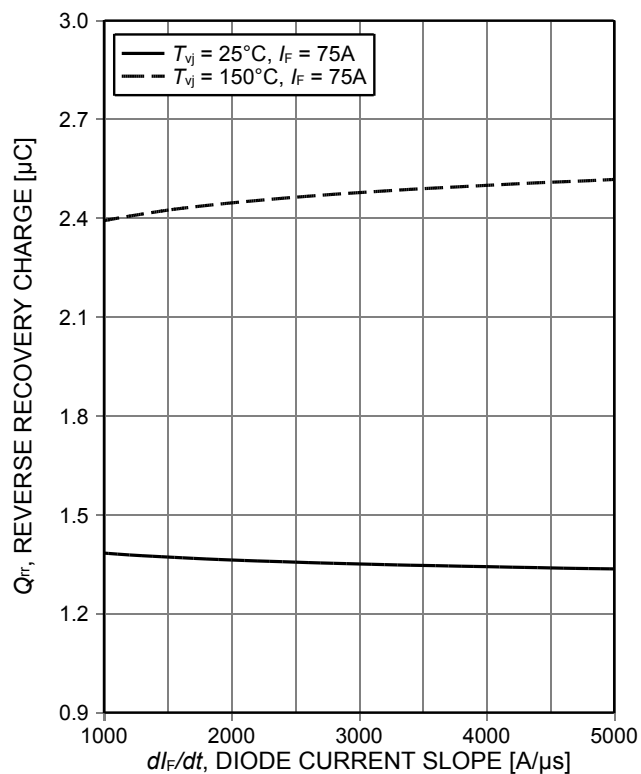
Low  $V_{CE(sat)}$  series fifth generation

Figure 21. Typical reverse recovery charge as a function of diode current slope ( $V_R=400V$ )

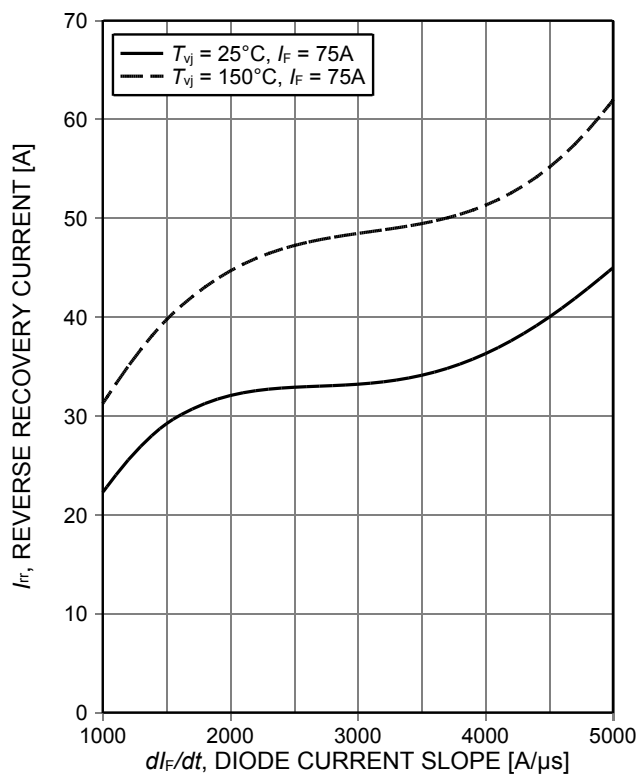


Figure 22. Typical reverse recovery current as a function of diode current slope ( $V_R=400V$ )

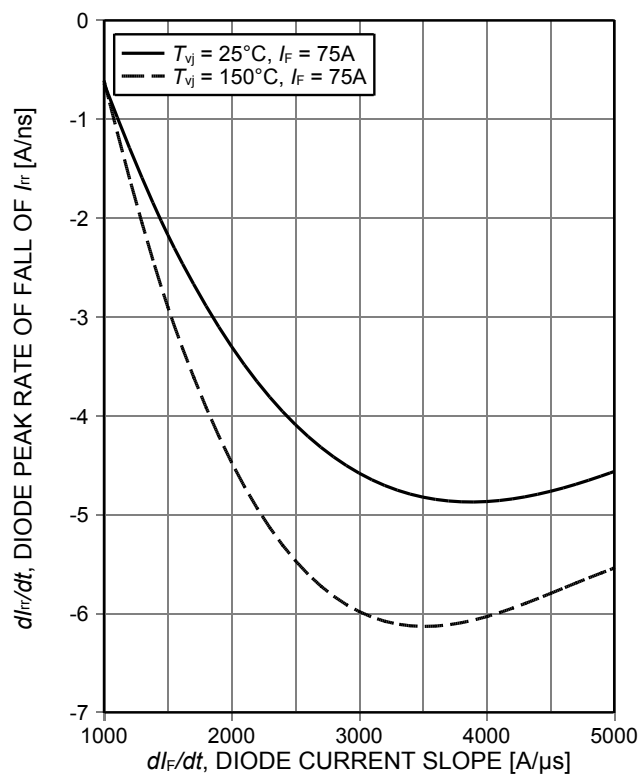


Figure 23. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope ( $V_R=400V$ )

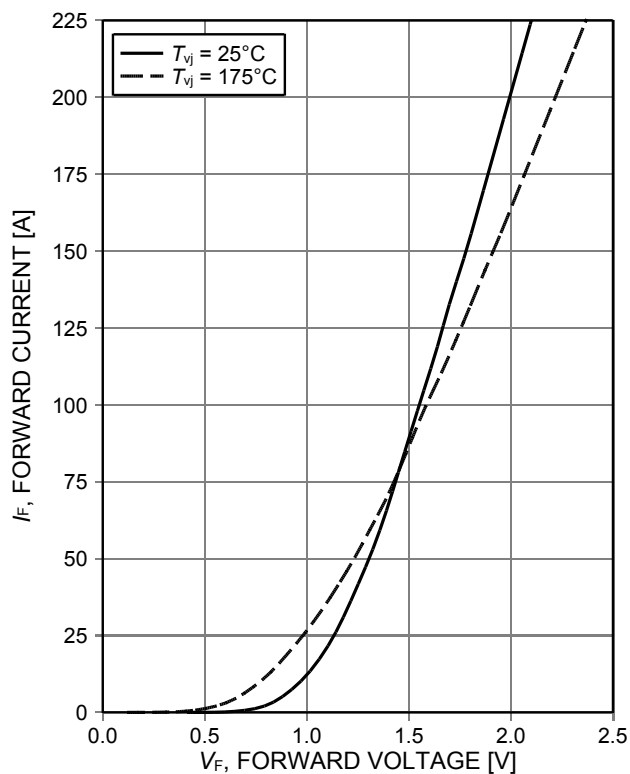


Figure 24. Typical diode forward current as a function of forward voltage

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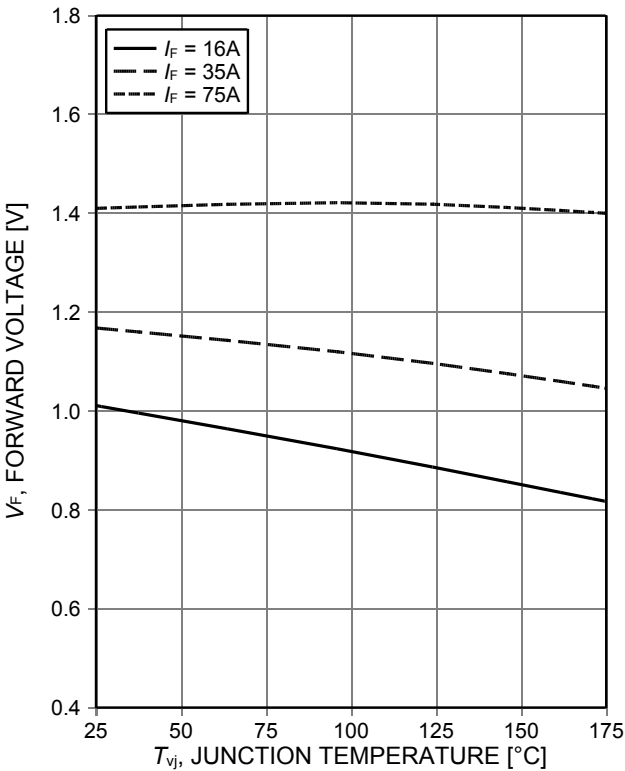
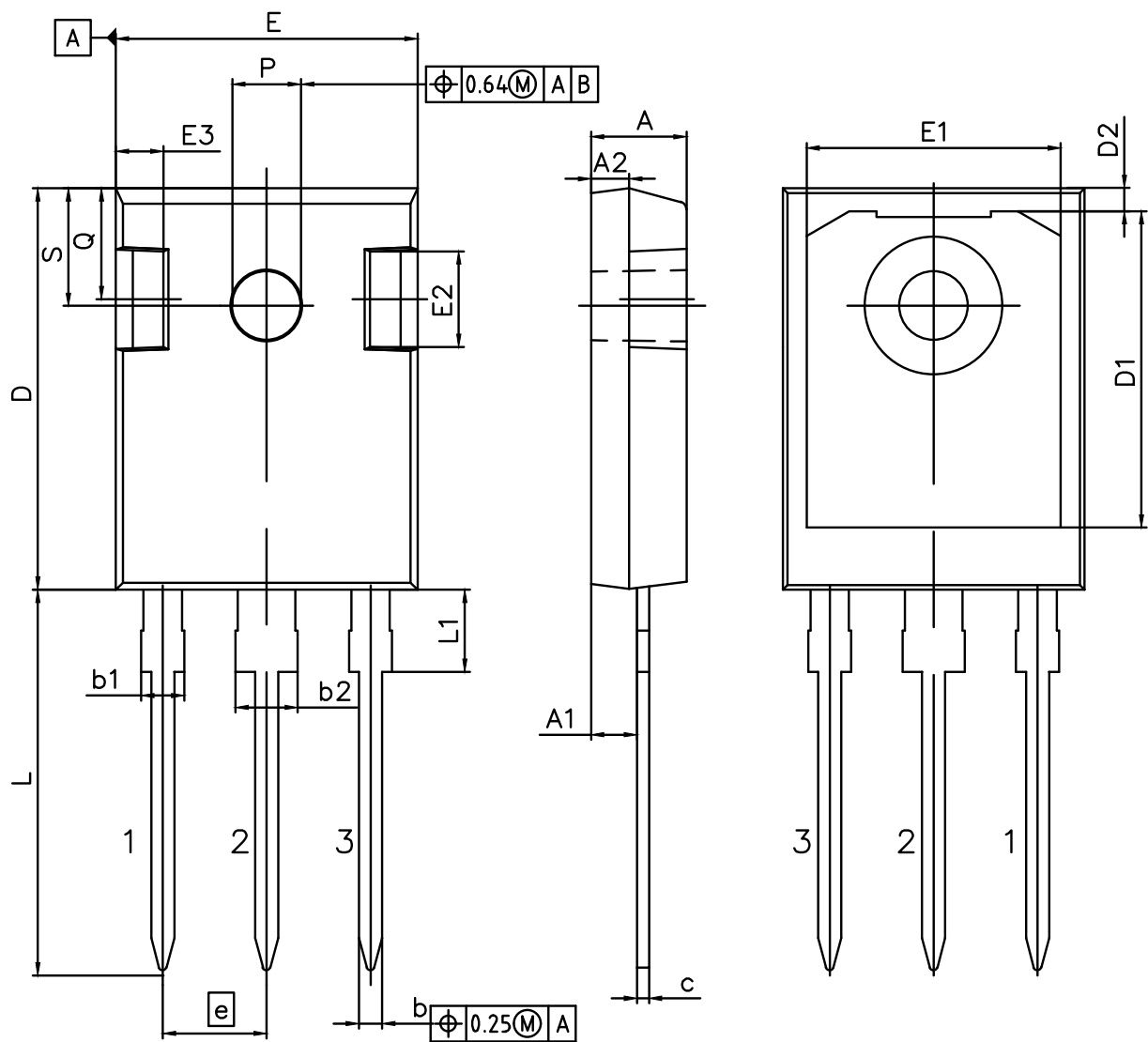


Figure 25. **Typical diode forward voltage as a function of junction temperature**

Low  $V_{CE(sat)}$  series fifth generation

Package Drawing PG-TO247-3



| DIMENSIONS | MILLIMETERS |       |
|------------|-------------|-------|
|            | MIN.        | MAX.  |
| A          | 4.70        | 5.30  |
| A1         | 2.20        | 2.60  |
| A2         | 1.50        | 2.50  |
| b          | 1.00        | 1.40  |
| b1         | 1.60        | 2.41  |
| b2         | 2.57        | 3.43  |
| c          | 0.38        | 0.89  |
| D          | 20.70       | 21.50 |
| D1         | 13.08       | 17.65 |
| D2         | 0.51        | 1.35  |
| E          | 15.50       | 16.30 |
| E1         | 12.38       | 14.15 |
| E2         | 3.40        | 5.10  |
| E3         | 1.00        | 2.60  |
| e          | 5.44        |       |
| L          | 19.80       | 20.40 |
| L1         | 3.85        | 4.50  |
| P          | 3.50        | 3.70  |
| Q          | 5.35        | 6.25  |
| S          | 6.04        | 6.30  |

**DOCUMENT NO.**  
Z8B00003327

**REVISION**  
06

**SCALE 3:1**  
0 1 2 3 4 5mm

**EUROPEAN PROJECTION**

**ISSUE DATE**  
25.07.2018

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## Testing Conditions

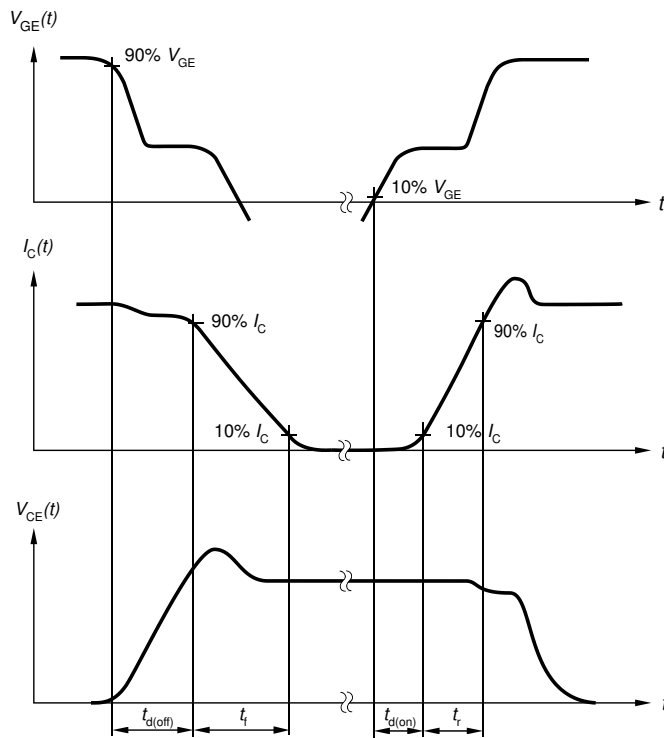


Figure A. Definition of switching times

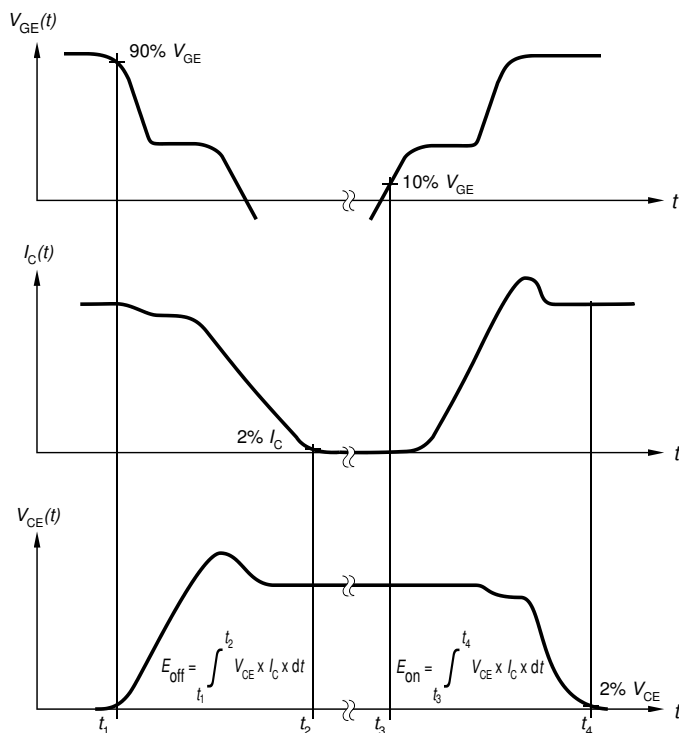


Figure B. Definition of switching losses

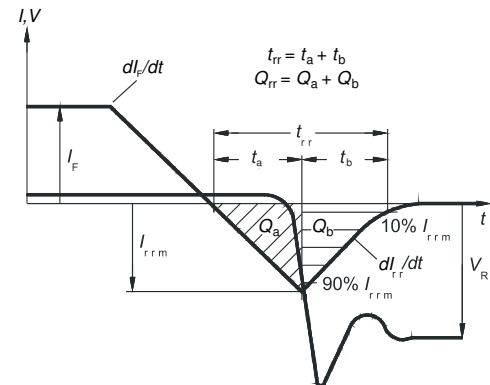


Figure C. Definition of diode switching characteristics

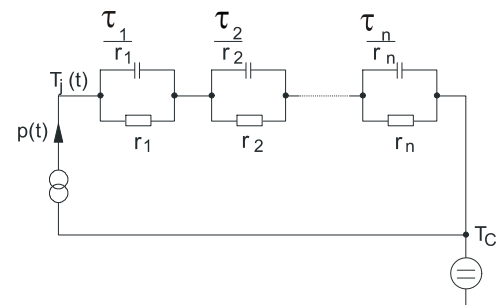


Figure D. Thermal equivalent circuit

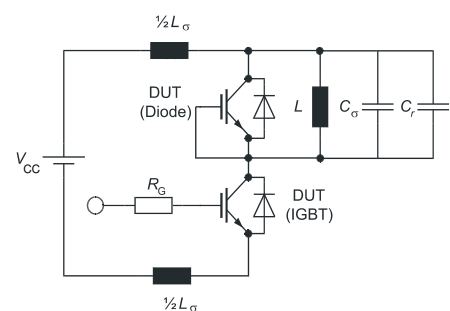


Figure E. **Dynamic test circuit**  
 Parasitic inductance  $L_{\sigma}$ ,  
 parasitic capacitor  $C_{\sigma}$ ,  
 relief capacitor  $C_r$ ,  
 (only for ZVT switching)

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#### Revision History

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IKW75N65EL5

**Revision: 2020-10-07, Rev. 2.2**

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Previous Revision

| Revision | Date       | Subjects (major changes since last revision) |
|----------|------------|----------------------------------------------|
| 2.1      | 2014-12-10 | Final data sheet                             |
| 2.2      | 2020-10-07 | VGE(th): test condition update               |

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